Attorney Docket No.: YOR920030604US

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AUG 0 9 2004

THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application

Applicant(s): Luk et al.

Docket No:

YOR920030604US1

Serial No.:

10/751,713

Filing Date:

January 5, 2004

Group:

2818

Examiner:

Unassigned

Title:

3T1D MEMORY CELLS USING GATED DIODES AND METHODS OF

USE THEREOF

INFORMATION DISCLOSURE STATEMENT

Commissioner of Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§1.56, 1.97 and 1.98, Applicants' attorney wishes to bring to the attention of the Patent and Trademark Office the following documents listed on the accompanying PTO Form 1449.

Other Documents

- 1. Luk et al., "Gated Diode Memory Cells," Serial Number 10/735,061 (filed December 11, 2003).
- 2. Luk et al., "Amplifiers Using Gated Diodes," Serial Number 10/751,714 (filed January 5, 2004).

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The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made, or as an admission that the information cited is considered to be material to patentability or as a representation that no other material information exists.

Respectfully submitted,

Date: August 5, 2004

Robert J. Mauri Attorney for Applicant(s) Reg. No. 41,180 Ryan, Mason & Lewis, LLP 1300 Post Road, Suite 205 Fairfield, CT 06824 (203) 255-6560

FORM PTO-1449 (MODIFIED)

Applicant.

LIST OF PUBLICATIONS FOR 0 9 2004 APPLICANT'S INFORMATION DISCLOSURE STATEMENT

Applicant(s): Luk et al. Docket No.: YOR9200

YOR920030604US1

Serial No.: Filing Date:

10/751,713 January 5, 2004

Group: 2818

| | | | U.S. PATENT DOCUM | MENTS | |
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| EXAMINER INITIAL | DOCUMENT NO. | DATE | NAME | CLASS/SUBCLASS | FILING DATE IF APPROPRIATE |
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| | Luk et al., "Gated Diode Memory Cells," Serial No. 10/735,061 (filed December 11, 2003). | | | | |
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